

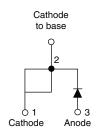
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Vishay Semiconductors

# HEXFRED® Ultrafast Soft Recovery Diode, 8 A



TO-247AC modified



PRODUCT SUMMARY						
Package	TO-247AC modified (2 pins)					
I <sub>F(AV)</sub>	8 A					
$V_{R}$	1200 V					
V <sub>F</sub> at I <sub>F</sub>	2.4 V					
t <sub>rr</sub> typ.	28 ns					
T <sub>J</sub> max.	150 °C					
Diode variation	Single die					

### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS
COMPLIANT
HALOGEN
FREE
Available

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

#### **DESCRIPTION**

VS-HFA08PB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	$V_{R}$		1200	V		
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8			
Single pulse forward current	I <sub>FSM</sub>		130	Α		
Maximum repetitive forward current	I <sub>FRM</sub>		32			
Maximum nauga discination	P <sub>D</sub>	T <sub>C</sub> = 25 °C	73.5	W		
Maximum power dissipation		T <sub>C</sub> = 100 °C	29			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		



# VS-HFA08PB120PbF, VS-HFA08PB120-N3

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA	1200	-	-			
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 8.0 A	See fig. 1	-	2.6	3.3	V	
		I <sub>F</sub> = 16 A		-	3.4	4.3		
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125 °C		-	2.4	3.1		
Maximum reverse	1	$V_R = V_R$ rated	See fig. 2	-	0.31	10		
leakage current	I <sub>RM</sub>	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See lig. 2	-	135	1000	μA	
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	-	11	20	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body		-	8.0	-	nH	

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
_	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200$	0 A/μs, V <sub>R</sub> = 30 V	-	28	-		
Reverse recovery time See fig. 5, 10	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	63	95	ns	
000 lig. 0, 10	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	106	160		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.5	8.0	A nC	
See fig. 6	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	6.2	11		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	140	380		
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	335	880	IIC	
Peak rate of recovery current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	133	-		
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	85	_	A/μs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.7		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	R <sub>thJA</sub> Typical socket mount		-	40	K/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.25	-		
Woight			-	6.0	-	g	
Weight			-	0.21	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC modified (JEDEC)		HFA08	PB120	•	

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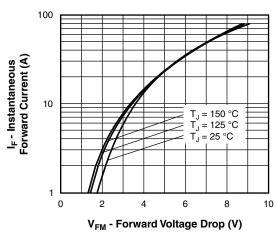


Fig. 1 - Maximum Forward Voltage Drop Characteristics

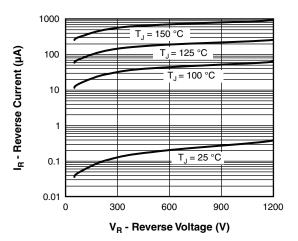


Fig. 2 - Values of Reverse Current vs. Reverse Voltage

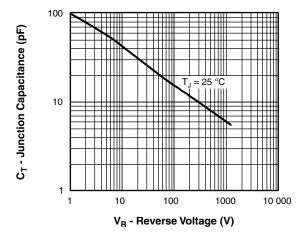


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

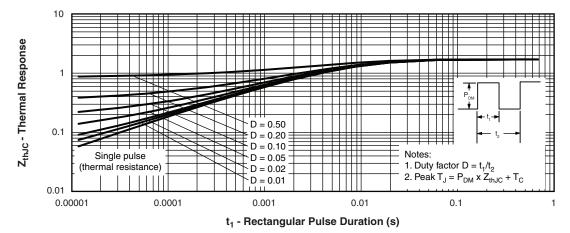


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics



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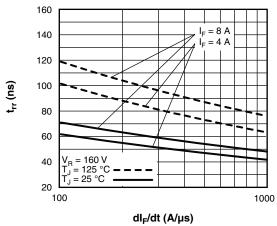


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

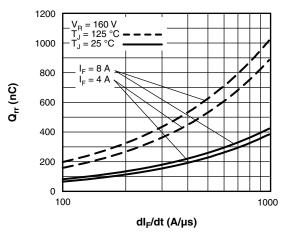


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

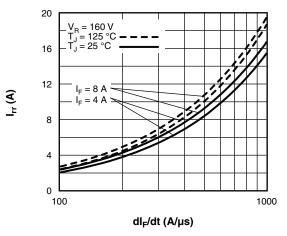


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

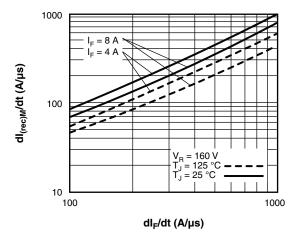


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 

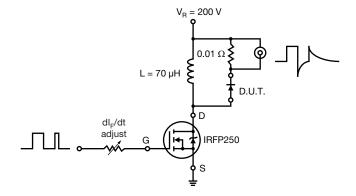
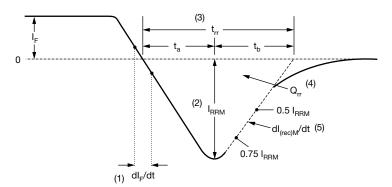


Fig. 9 - Reverse Recovery Parameter Test Circuit

# VS-HFA08PB120PbF, VS-HFA08PB120-N3

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- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

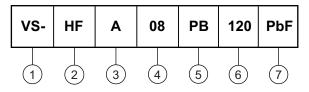
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dI<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

**Device code** 



- 1 Vishay Semiconductors product
- 2 HEXFRED® family
- 3 Electron irradiated
- 4 Current rating (08 = 8A)
- 5 PB = TO-247AC modified
- Voltage rating: (120 = 1200 V)
- 7 Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA08Pb120PbF	25	500	Antistatic plastic tube				
VS-HFA08Pb120-N3	25	500	Antistatic plastic tube				

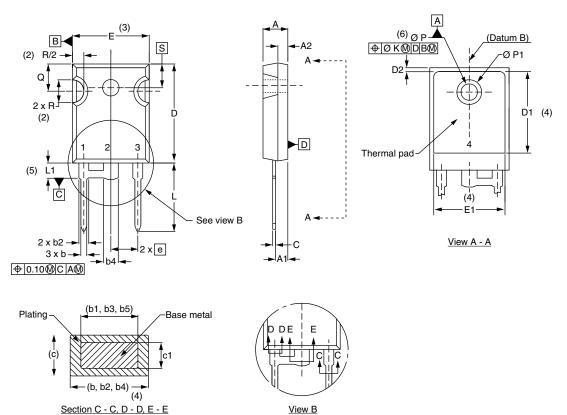
LINKS TO RELATED DOCUMENTS						
Dimensions		www.vishay.com/doc?95541				
Part marking information	TO-247AC modified PbF	www.vishay.com/doc?95255				
Fart marking information	TO-247AC modified -N3	www.vishay.com/doc?95442				



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### TO-247AC modified - 50 mils L/F

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
С	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
OTIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.35	0.020	0.053	
Е	15.29	15.87	0.602	0.625	3
E1	13.46	=.	0.53	-	
е	5.46 BSC		0.215	BSC	
ØK	0.254		0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51	5.51 BSC		0.217 BSC	

#### Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



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